

PATENT
452080-2010

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Hans Meiling et al.
Filed: August 5, 1999
Title of Invention: SEMICONDUCTING DEVICES AND METHOD
OF MAKING THEREOF

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INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Box PATENT APPLICATION
Washington, D.C. 20231

Sir:

Applicants bring to the attention of the Examiner the
prior art cited in the parent application, serial no. 09/331,528.
Also enclosed is a copy of Form PTO-1449.

REMARKS

Entry of this Information Disclosure Statement and an
early examination on the merits are respectfully solicited.

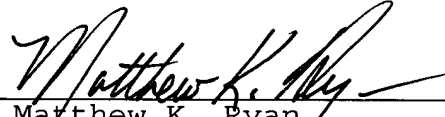


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452080-2010

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Respectfully submitted,

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Based on Form PTO-1449 (3/90)	ATTY. DOCKET NO. 452080-2010	SERIAL NO. 09/331,528
	APPLICANT Hans Meiling et al.	
	FILING DATE August 5, 1999	GROUP 2814

LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)

J1033 U.S. PTO
09/852999

05/10/01

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLAS S	FILING DATE IF APPROPRIATE
	AA	4,634,605	01/6/1987	Wiesman			
	AB	4,485,128	11/24/84	Dala et al.			
	AC	4,465,706	8/14/84	Dala et al.			
	AD	5,397,737	3/14/84	Mahan et al.			
	AE	5,500,047	3/19/96	Park et al.			
	AF	5,776,819	7/7/98	Mahan et al.			
	AG	5,798,137	08/25/98	Lord et al.			
	AH	5,281,546	1/25/94	Possin et al.			
	AI	4,747,077	5/24/88	Hockley et al.			
	AJ	4,237,151	12/2/80	Strongin et al.			
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AL	0 687 753	12/20/95	Europe			
	AM	43 33 416	4/6/95	Germany			
	AN						
	AO						
	AP						

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AQ	Meiling H. et al., "Stability of hot-wire deposited amorphous-silicon thin-film transistors". Applied Physics Letters, 19 August 1996, AIP, USA, vol. 69, no. 8, ISSN 0003-6951, pages 1062-1064, XP000626137
	AR	Kikuo Ono et al., "Inverse-Staggered Polycrystalline Silicon thin Film Transistors Fabricated By Excimer Laser Irradiation". Electronics & vol. 76, no. 12, December, 1993, pages 40-46, XP000468568
	AS	Doyle R. et al., "Production of high-quality amorphous silicon films by evaporative silane surface decomposition". Journal of Applied Physics, 15 Sept. 1988, USA, vol. 64, no. 6, ISSN 0021-8979, pages 3215-3223, XP000097188
	AT	Japanese Abstract of 01-162769, dated June 27, 1989; Araki Makoto: FORMATION OF AMORPHOUS SILICON

EXAMINER	DATE CONSIDERED
<p>* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	